NCP1406, NCV1406

Boost Converter - PFM, DC-DC

25 V, 25 mA

The NCP1406 is a monolithic step-up DC-DC converter operating in a Pulse Frequency Modulation (PFM) scheme with constant peak current control. It integrates a 0.8 A, 0.7 Ω internal power switch and sensing resistor to monitor inductor current. This control scheme maintains high efficiencies over the entire load current range. The wide input voltage range, from 1.4 V to 5.5 V, enables the user to operate the device from a Li-Ion battery or a two-cell Alkaline NiMH. Its ability to boost voltages up to 25 V, and to provide 1 W output power, makes the NCP1406 the perfect solution for biasing small and large OLED panels. This device also makes a perfect solution for biasing a great number of white LEDs in series. A Chip Enable pin allows the user to control the device to extend the battery life during standby, and can be pulse-width modulated for white LED applications. The versatility of the NCP1406 allows it to be configured not only as a step-up converter, but also as an inverter and as a step-down converter. This solution is proposed in a space-saving TSOP-5 package.

Features

• 87% Efficiency at VOUT = 25 V, IOUT = 25 mA, VIN = 5 V
• Adjustable Output Voltage up to 25 V
• 0.8 A, 26 V Internal Power Switch
• Operating Input Voltage from 1.4 V to 5.5 V
• Low Startup Voltage of 1.8 V Typical at No Load
• Low Operating Current of 15 μA (Not Switching)
• Low Shutdown Current of 0.3 μA
• Operating Switching Frequency up to 1 MHz
• Output Voltage Soft-Start
• Thermal Shutdown Protection
• These are Pb-Free Devices
• NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

Typical Applications

• LCD Bias Supplies
• Small and Large OLED Display Drivers
• White LED Driver for Backlight Displays
• Personal Digital Assistants (PDA)
• Portable Applications:
  ♦ Cell Phones, Digital Cameras
  ♦ PDAs, Games, and Portable Video Players

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Figure 1. Typical Application Circuit

Figure 2. Efficiency versus Output Current

Figure 3. Typical 25 V Step–Up Application Circuit

Figure 4. Typical 15 V Step–Up Application Circuit
**NCP1406, NCV1406**

![Typical 8 V Step-Up Application Circuit](image)

Figure 5. Typical 8 V Step-Up Application Circuit

![Representative Block Diagram](image)

Figure 6. Representative Block Diagram

**PIN FUNCTION DESCRIPTION**

<table>
<thead>
<tr>
<th>Pin</th>
<th>Symbol</th>
<th>Description</th>
</tr>
</thead>
</table>
| 1   | CE     | Chip Enable Pin  
(1) The chip is enabled if a voltage which is equal to or greater than 0.9 V is applied.  
(2) The chip is disabled if a voltage which is less than 0.3 V is applied.  
(3) The chip will be enabled if it is left floating. |
| 2   | FB     | Output feedback voltage. Connected to the inverting input of the PFM comparator. |
| 3   | VDD    | Power supply pin for internal circuit |
| 4   | GND    | Analog and power ground pin |
| 5   | LX     | External inductor connection pin. Connected to the drain of the NMOS internal switch. |
### MAXIMUM RATINGS

<table>
<thead>
<tr>
<th>Rating</th>
<th>Symbol</th>
<th>Value</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>Power Supply Voltage (Pin 3)</td>
<td>VDD</td>
<td>−0.3 to 6.0</td>
<td>V</td>
</tr>
<tr>
<td>Input/Output Pin</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>LX (Pin 5)</td>
<td>V_{LX}</td>
<td>−0.3 to 27</td>
<td>V</td>
</tr>
<tr>
<td>LX Peak Sink Current</td>
<td>I_{LX}</td>
<td>1.5</td>
<td>A</td>
</tr>
<tr>
<td>FB (Pin 2)</td>
<td>V_{FB}</td>
<td>−0.3 to 6.0</td>
<td>V</td>
</tr>
<tr>
<td>CE (Pin 1)</td>
<td>V_{CE}</td>
<td>−0.3 to 6.0</td>
<td>V</td>
</tr>
<tr>
<td>Power Dissipation and Thermal Characteristics</td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Maximum Power Dissipation @ T_A = 25°C</td>
<td>P_D</td>
<td>500</td>
<td>mW</td>
</tr>
<tr>
<td>Thermal Resistance, Junction–to–Air</td>
<td>R_{JUA}</td>
<td>250</td>
<td>°C/W</td>
</tr>
<tr>
<td>Operating Ambient Temperature Range</td>
<td>T_A</td>
<td>−40 to +85, −40 to +105</td>
<td>°C</td>
</tr>
<tr>
<td>Operating Junction Temperature Range</td>
<td>T_J</td>
<td>−40 to +150</td>
<td>°C</td>
</tr>
<tr>
<td>Storage Temperature Range</td>
<td>T_{stg}</td>
<td>−55 to +150</td>
<td>°C</td>
</tr>
</tbody>
</table>

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. This device series contains ESD protection and exceeds the following tests:
   - Human Body Model (HBM): ±2.0 kV per JEDEC standard: JESD22–A114 for all pins
   - Machine Model (MM): ±200 V per JEDEC standard: JESD22–A115 for all pins
2. Latchup Current Maximum Rating: ±150 mA per JEDEC standard: JESD78

### DISSIPATION RATINGS

<table>
<thead>
<tr>
<th>Package</th>
<th>Power Rating @T_A = 25°C</th>
<th>Derating Factor @T_A &gt; 25°C</th>
<th>Power Rating @T_A = 70°C</th>
<th>Power Rating @T_A = 85°C</th>
<th>Power Rating @T_A = 105°C</th>
</tr>
</thead>
<tbody>
<tr>
<td>TSOP–5</td>
<td>500 mW</td>
<td>4.0 mW/°C</td>
<td>320 mW</td>
<td>260 mW</td>
<td>180 mW</td>
</tr>
</tbody>
</table>

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### ELECTRICAL CHARACTERISTICS

\( (V_{OUT} = 25\, V, \, T_A = -40\, ^\circ C\, \text{to}\, +85\, ^\circ C\, (NCP1406), \, T_A = -40\, ^\circ C\, \text{to}\, +105\, ^\circ C\, (NCV1406) \) for min/max values, typical values are at \( T_A = 25\, ^\circ C \), unless otherwise noted.

<table>
<thead>
<tr>
<th>Characteristic</th>
<th>Symbol</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>ON/OFF TIMING CONTROL</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Minimum Off Time (( V_{DD} = 3.0, V, , V_{FB} = 0, V ))</td>
<td>( t_{off} )</td>
<td>0.08</td>
<td>0.13</td>
<td>0.20</td>
<td>( \mu s )</td>
</tr>
<tr>
<td>Maximum On Time (Current Not Asserted)</td>
<td>( t_{on} )</td>
<td>0.58</td>
<td>0.90</td>
<td>1.40</td>
<td>( \mu s )</td>
</tr>
<tr>
<td>Maximum Duty Cycle</td>
<td>( D_{MAX} )</td>
<td>84</td>
<td>90</td>
<td>96</td>
<td>%</td>
</tr>
<tr>
<td>Minimum Startup Voltage (( I_{OUT} = 0, mA ))</td>
<td>( V_{start} )</td>
<td>–</td>
<td>1.8</td>
<td>2.0</td>
<td>V</td>
</tr>
<tr>
<td>Minimum Startup Voltage Temperature Coefficient (( T_A = -40 , \text{to}, +105, ^\circ C ))</td>
<td>( \Delta V_{start} )</td>
<td>–</td>
<td>1.6</td>
<td>–</td>
<td>mV/°C</td>
</tr>
<tr>
<td>Minimum Hold Voltage (( I_{OUT} = 0, mA ))</td>
<td>( V_{hold} )</td>
<td>–</td>
<td>1.7</td>
<td>1.9</td>
<td>V</td>
</tr>
<tr>
<td>Soft-Start Time</td>
<td>( t_{SS} )</td>
<td>–</td>
<td>3.0</td>
<td>8.0</td>
<td>ms</td>
</tr>
<tr>
<td>LX (PIN 5)</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Internal Switch Voltage (Note 4) (Note 5)</td>
<td>( V_{LX} )</td>
<td>–</td>
<td>–</td>
<td>26</td>
<td>V</td>
</tr>
<tr>
<td>LX Pin On-State Resistance (( V_{LX} = 0.4, V, , V_{DD} = 5.0, V ))</td>
<td>( R_{sw(on)} )</td>
<td>–</td>
<td>0.7</td>
<td>–</td>
<td>Ω</td>
</tr>
<tr>
<td>Current Limit (When ( I_{LX} ) reaches ( I_{LIM} ), the LX switch is turned off by the LX switch protection circuit) (Note 5)</td>
<td>( I_{LIM} )</td>
<td>–</td>
<td>0.80</td>
<td>–</td>
<td>A</td>
</tr>
<tr>
<td>Off-State Leakage Current (( V_{LX} = 26, V ))</td>
<td>( I_{LKG} )</td>
<td>–</td>
<td>0.1</td>
<td>1.0</td>
<td>( \mu A )</td>
</tr>
<tr>
<td>CE (PIN 1)</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>CE Input Voltage (( V_{DD} = 3.0, V, , V_{FB} = 0, V ))</td>
<td>High State, Device Enabled</td>
<td>( V_{CE(high)} )</td>
<td>0.9</td>
<td>–</td>
<td>–</td>
</tr>
<tr>
<td>Low State, Device Disabled</td>
<td>( V_{CE(low)} )</td>
<td>–</td>
<td>–</td>
<td>0.3</td>
<td>V</td>
</tr>
<tr>
<td>CE Input Current</td>
<td>High State, Device Enabled (( V_{DD} = V_{CE} = 5.5, V ))</td>
<td>( I_{CE(high)} )</td>
<td>–</td>
<td>10</td>
<td>–</td>
</tr>
<tr>
<td>Low State, Device Disabled (( V_{DD} = 5.5, V, , V_{CE} = V_{FB} = 0, V ))</td>
<td>( I_{CE(low)} )</td>
<td>–</td>
<td>–</td>
<td>150</td>
<td>–</td>
</tr>
<tr>
<td>TOTAL DEVICE</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Supply Voltage</td>
<td>( V_{DD} )</td>
<td>1.4</td>
<td>–</td>
<td>5.5</td>
<td>V</td>
</tr>
<tr>
<td>Undervoltage Lockout (( V_{DD} ) Falling)</td>
<td>( V_{UVLO} )</td>
<td>–</td>
<td>1.0</td>
<td>1.3</td>
<td>V</td>
</tr>
<tr>
<td>Feedback Voltage</td>
<td>( T_A = 25, ^\circ C )</td>
<td>( V_{FB} )</td>
<td>1.178</td>
<td>1.190</td>
<td>1.202</td>
</tr>
<tr>
<td>( T_A = -40 , \text{to}, +105, ^\circ C )</td>
<td>–</td>
<td>1.170</td>
<td>1.190</td>
<td>1.210</td>
<td>V</td>
</tr>
<tr>
<td>Feedback Pin Bias Current (( V_{FB} = 1.19, V ))</td>
<td>( I_{FB} )</td>
<td>–</td>
<td>15</td>
<td>45</td>
<td>nA</td>
</tr>
<tr>
<td>Operating Current 1 (( V_{FB} = 0, V, , V_{DD} = V_{CE} = 3.0, V, , \text{Maximum Duty Cycle} ))</td>
<td>( I_{DD1} )</td>
<td>–</td>
<td>0.7</td>
<td>1.5</td>
<td>mA</td>
</tr>
<tr>
<td>Operating Current 2 (( V_{DD} = V_{CE} = V_{FB} = 3.0, V, , \text{Not Switching} ))</td>
<td>( I_{DD2} )</td>
<td>–</td>
<td>15</td>
<td>25</td>
<td>( \mu A )</td>
</tr>
<tr>
<td>Off-State Current (( V_{DD} = 5.0, V, , V_{CE} = 0, V ))</td>
<td>( I_{OFF} )</td>
<td>–</td>
<td>0.3</td>
<td>1.3</td>
<td>( \mu A )</td>
</tr>
<tr>
<td>Thermal Shutdown (Note 5)</td>
<td>( T_{SD} )</td>
<td>–</td>
<td>140</td>
<td>–</td>
<td>°C</td>
</tr>
<tr>
<td>Thermal Shutdown Hysteresis (Note 5)</td>
<td>( T_{SDHY} )</td>
<td>–</td>
<td>10</td>
<td>–</td>
<td>°C</td>
</tr>
</tbody>
</table>

4. Recommended maximum \( V_{OUT} \) up to 25 V.
5. Guaranteed by design, not tested.
TYPICAL CHARACTERISTICS

Figure 7. Efficiency versus Output Current
(V_{OUT} = 25 V, L = 8.2 \mu H)

Figure 8. Efficiency versus Output Current
(V_{OUT} = 25 V, L = 10 \mu H)

Figure 9. Efficiency versus Output Current
(V_{OUT} = 15 V, L = 8.2 \mu H)

Figure 10. Efficiency versus Output Current
(V_{OUT} = 15 V, L = 10 \mu H)

Figure 11. Efficiency versus Output Current
(V_{OUT} = 8.0 V, L = 8.2 \mu H)

Figure 12. Efficiency versus Output Current
(V_{OUT} = 8.0 V, L = 10 \mu H)
TYPICAL CHARACTERISTICS

Figure 13. Feedback Voltage versus Ambient Temperature

Figure 14. Maximum On Time versus Ambient Temperature

Figure 15. Minimum Off Time versus Ambient Temperature

Figure 16. Operating Current 1 versus Ambient Temperature

Figure 17. Operating Current 2 versus Ambient Temperature

Figure 18. Off-State Current versus Ambient Temperature
TYPICAL CHARACTERISTICS

Figure 19. Soft-start Time versus Ambient Temperature

Figure 20. No Load Input Current versus Input Voltage

Figure 21. Current Limit versus Ambient Temperature

Figure 22. Switch-ON Resistance versus Input Voltage

Figure 23. Load Transient Response (V_{OUT} = 15 V)

Figure 24. Line Transient Response (V_{OUT} = 15 V)
TYPICAL CHARACTERISTICS

Figure 25. Operating Waveforms (Light Load)

Figure 26. Operating Waveforms (Heavy Load)

Figure 27. Startup/Shutdown Waveforms (VOUT = 25 V)

Figure 28. Startup/Shutdown Waveforms (VOUT = 15 V)

Figure 29. Startup Voltage versus Input Voltage (VOUT = 25 V)

Figure 30. Startup Voltage versus Input Voltage (VOUT = 15 V)
SIMPLIFIED OPERATING DESCRIPTION

Operation

The NCP1406 is a monolithic DC−DC switching converter optimized for single Lithium, two− or three−cell AA/AAA size battery−powered portable products.

The NCP1406 operates in a Pulse Frequency Modulation (PFM) scheme with constant peak current control. This scheme maintains high efficiencies over the entire load current range.

The device is designed to operate in Discontinuous Conduction Mode (DCM). When the inductor releases its energy to the output and its current reaches zero before a new cycle starts, the converter is said to operate in DCM. If a new cycle starts before the inductor current reaches zero, the converter is said to operate in Continuous Conduction Mode (CCM).

The operation of the NCP1406 is not limited to the discontinuous conduction mode. The device can also be operated in continuous conduction mode, but its stability is not guaranteed.

Figure 31 depicts the three phases of operation in DCM in a simplified way. During the first interval, the switch is turned on and the diode is reverse biased. The inductor stores energy through the battery while the load is supplied by the output capacitor to maintain regulation. During the second interval, the switch is turned off and the diode is forward biased, this allows the energy stored in the inductor to be supplied to both the load and the capacitor. During the third interval, the switch is kept off and the diode is reverse biased, the capacitor supplies the current to the load.

In DCM, the voltage ratio can be expressed as:

\[
\frac{V_{OUT}}{V_{IN}} = \frac{1 + \sqrt{1 + \frac{4 \times D \times K D}{K}}}{2} \tag{eq. 1}
\]

Where \( D = \frac{TON}{TSW} \), \( KD = 2 \times L \times \frac{I_{OUT}}{V_{OUT} \times TSW} \)

Unlike in CCM, the voltage ratio of a boost converter in DCM is load dependent.
The detailed operation of NCP1406 can be best understood by referring to the block diagram and typical application circuits in Figures 1, 3, 4, and 5. The PFM comparator monitors the output voltage via the external feedback resistor divider by comparing the feedback voltage with the reference voltage. When the feedback voltage is lower than the reference voltage, the PFM controller and driver circuit turn the internal switch on and the current ramps up in the inductor. The switch will remain on for the maximum on–time, 0.90 μs, or until the current limit is reached (0.8 A), whichever occurs first. The internal switch is then turned off and the inductor current ramps down. The energy stored in the inductor will be discharged to the output capacitor and load through the Schottky diode. The internal switch will be turned off for at least the minimum off–time, 0.13 μs, and will remain off until the feedback voltage becomes lower than the reference voltage. If the inductor current reaches zero before then, the Schottky diode will be reverse biased and the output capacitor will sustain the regulation by providing current to the load, while the switch pin will be left floating. The switch will turn back on when the feedback voltage becomes again lower than reference voltage. This switching cycle is then repeated to attain voltage regulation. The device operating current is typically 15 μA (not switching), and can be further reduced to about 0.3 μA when the chip is disabled (VCE < 0.3 V).

**Soft Start**
There is a soft start circuit in NCP1406. When power is applied to the device, the soft–start circuit limits the device to switch at a small duty cycle initially. The duty cycle is then increased gradually until the output voltage is in regulation. With the soft–start circuit, the output voltage over–shoot is minimized and the startup capability with heavy loads is also improved.

**ON/OFF Timing Control**
The timing control of the converter is application dependent. The maximum on–time (inductor current ramping up) is set at a typical 0.9 μs if the inductor current does not reach current limit 0.8 A. The minimum off–time (inductor current ramping down) is set at a typical 0.13 μs to ensure the complete energy transfer to the output. The switching frequency can be as high as 1.0 MHz.

**Voltage Reference and Output Voltage**
The internal bandgap voltage reference is trimmed to 1.19 V with an accuracy of ± 1.0% at 25°C. The voltage reference is connected to the non inverting input of the PFM comparator and the inverting input of the PFM comparator is connected to the FB pin. The output voltage can be set by connecting an external resistor divider to the output and using the FB pin. The output voltage programmable range is from VIN to 25 V.

**Current Limit**
The current limit circuit limits the maximum current flowing through the LX pin to a typical 0.8 A during the internal switch turn–on period. When the current limit is exceeded, the switch will be turned off. Since the peak inductor current is limited to the current limit, saturation of inductor is prevented and output voltage over–shoot during startup is also minimized.

**Internal Switch**
The NCP1406 integrates a 26 V open drain internal switch which allows high output voltage up to 25 V to be generated from simple step–up topology.

**FB Pin Short–Circuit/Open–Circuit Protection**
The FB protection circuit is realized by sensing the drain–to–source leakage current of the N–Ch MOSFET. When the FB pin connection is shorted or opened, the converter switches at maximum duty cycle, the peak of V_{LX} and the V_{OUT} will build up, and the leakage current will increase. When the leakage current increases to a certain level, the protection circuitry will trigger and the converter will stop switching. Therefore, the peak of V_{LX} will immediately stop increasing at a certain level before the N–Ch MOSFET is damaged. However, the sensing of the leakage current is not very accurate and cannot be too close to the normal 26 V maximum operating condition. Therefore, the VLX is around 30 V to 40 V during a FB pin protection fault. This is not destructive to the chip though.

**Input Undervoltage Lockout**
An undervoltage lockout circuit continuously monitors the voltage at the VDD pin. The device will be disabled if the VDD pin voltage drops below the UVLO threshold voltage. In the same manner, the device will be enabled if the VDD pin voltage goes above the UVLO threshold.

**Thermal Shutdown**
When the chip junction temperature exceeds 140°C, the entire IC is shutdown. The IC will resume operation when the junction temperature drops below 130°C.

**Enable/Disable Operation**
An external pin, CE, allows the user to enable or disable the converter. This feature proves useful when the system is in a standby mode by increasing battery life through significantly decreased current consumption. A 150 nA pull–up current source ties the CE pin to the VDD pin internally. Therefore, leaving the CE pin floating will enable the NCP1406.

With no other connections to the CE pin, it can be independently controlled by an external signal. When the voltage at the CE pin is equal to or greater than 0.9 V, the chip will be enabled, which means the device is in normal operation. When the voltage at the CE pin is less than 0.3 V,
the chip is disabled and is shutdown. During shutdown, the IC supply current reduces to 0.3 μA and the LX pin enters high impedance state. However, the input remains connected to the output through the inductor and the Schottky diode, keeping the output voltage one diode forward voltage drop below the input voltage.

When the NCP1406 is used to drive white LEDs, the EN pin can be pulse width modulated to control LED brightness.

**External Component Selection**

**Inductor**

Because it uses a PFM peak current control scheme in DCM, the NCP1406 is inherently stable. The inductor value does not affect the stability of the device. The NCP1406 is designed to work well with a range of inductance values; the actual inductance value depends on the specific application, output current, efficiency, and output ripple voltage. For step-up conversion, the device works well with inductance ranging from 1 μH to 47 μH. The selection of the inductor value along with the load current, input and output voltages determines the switching frequency at which the converter will operate.

In general, an inductor with small DCR is used to minimize loss and increase efficiency. It is necessary to choose an inductor with saturation current greater than the peak switching current in the application.

A lower inductor value increases the switching frequency, hence increases the losses which yields a lower overall efficiency.

As stated before, the NCP1406 is designed to operate in DCM. Stable operation in CCM is not guaranteed.

For all the mathematical equations given below, \( V_{IN} \) is the input voltage, \( T_{ON\_MAX} \) is the maximum on-time which is typically 0.9 μs, \( I_{LIM} \) is the current limit which is typically 0.8 A, \( L \) is the selected inductance, \( V_{OUT} \) is the desired output voltage, \( V_D \) is the Schottky diode forward voltage, and \( \eta \) is the conversion efficiency which can be assumed typically 80% for better margin for estimation.

**Mode determination**

The on-time (inductor ramp up) can be expressed as following:

\[
T_{ON} = \frac{L}{V_{IN}} \times I_{PK} \quad \text{(eq. 2)}
\]

The output current and the switching frequency can be expressed as following:

\[
I_{OUT} = \frac{V_{IN} \times T_{ON}}{2 \times L} \times \frac{1}{(1-D_2-1)} + \frac{V_{OUT}+V_D}{\eta \times V_{IN}}
\]

\[
F_{SW} = \frac{T_{ON} \times (1 + \eta \frac{V_{IN}}{V_{OUT}+V_D} (1-D_2-1))}{(V_{OUT}+V_D) - 1}
\]

In the above equations, \( D_2 \) gives us the information about the mode of operation (DCM or CCM). The value of \( D_2 \) will increase as load increases until it reaches 1, which corresponds to the state of critical conduction when the inductor current starts ramping up immediately after it reaches zero (starting a new cycle).

The value of the output current and the switching frequency at the critical mode transition \( (D_2 = 1) \) can be expressed as following:

\[
I_{OUT} = \frac{V_{IN}^2 \times T_{ON}}{2 \times L \times (V_{OUT}+V_D)} \times \eta
\]

\[
F_{SW\_\text{load}} = \frac{2 \times L \times I_{OUT}}{V_{IN} \times T_{ON}^2} \times \left( \frac{V_{OUT}+V_D}{\eta \times V_{IN}} - 1 \right)
\]

One can determine the mode of operation using the factor \( I_{ROOM} \) defined as:

\[
I_{ROOM} = \frac{V_{IN}^2 \times T_{ON}}{2 \times L \times (V_{OUT}+V_D)} \times \eta - I_{OUT}
\]

If \( I_{ROOM} < 0 \), the converter operates in continuous conduction mode.

If \( I_{ROOM} = 0 \), the converter operates in critical conduction mode.

If \( I_{ROOM} > 0 \), the converter operates in discontinuous conduction mode.

**The Discontinuous Conduction Mode**

For each switching cycle, if the internal MOSFET is switched on, it will be switched off only when either the maximum on-time, \( T_{ON} \), of typical 0.9 μs is reached or the inductor current limit of 0.8 A is met, whichever is earlier. Therefore, the designer can choose to use either the maximum on–time or the current limit to turn off the internal switch.

**Minimizing the output ripple voltage**

If the aim is to minimize output ripple voltage, the maximum on–time of 0.9 μs should be used to turn off the MOSFET; however, the maximum output current will be reduced. It is critical to ensure that the maximum on–time has been reached before the current limit is met.

\[
T_{ON\_\text{MAX}} < \frac{L}{V_{IN}} \times I_{LIM}
\]

To ensure this condition is met, the inductance \( L \) should be selected according to the following equation:

\[
L > \frac{V_{IN}}{I_{LIM}} \times T_{ON\_\text{MAX}}
\]

http://onsemi.com
The switching frequency at nominal load is expressed as:

$$\text{FSW}(\text{load}) = \frac{2 \times L \times I_{\text{OUT}}}{V_{\text{IN}} \times T_{\text{ON MAX}}^2} \times \left(\frac{V_{\text{OUT}} + V_D}{\eta \times V_{\text{IN}}} - 1\right) \hspace{1cm} (\text{eq. 8})$$

The maximum output current under this maximum on–time control will be achieved at the limits of critical conduction mode and can be calculated from the equation below:

$$I_{\text{OUT MAX}} = \frac{V_{\text{IN}}^2 \times T_{\text{ON MAX}}}{2 \times L \times (V_{\text{OUT}} + V_D) \times \eta} \hspace{1cm} (\text{eq. 9})$$

The above equation for calculating $I_{\text{OUT MAX}}$ is for DCM mode operation only. The operation can go beyond the critical conduction mode if the current loading further increases above the maximum output current in DCM mode. However, stable operation in continuous conduction mode is hard to achieve. Refer below to the Continuous Conduction Mode section.

Maximizing the output current

If we target to maximize the output current, the current limit should be chosen to turn off the MOSFET, but this method will result in a larger output ripple voltage. It is critical to make sure that the current limit has been reached before the maximum on–time is met. To ensure this condition is met, the inductance $L$ should be selected according to the following equation:

$$L < \frac{V_{\text{IN}} \times T_{\text{ON MAX}}}{I_{\text{LIMIT}}} \hspace{1cm} (\text{eq. 10})$$

Since there are 100 ns internal propagation delay between the time the current limit is reached and the time the MOSFET is switched off, the actual peak inductor current can be obtained from the equation below:

$$I_{\text{PK}} = I_{\text{LIMIT}} + \frac{V_{\text{IN}}}{L} \times 100 \text{ ns} \hspace{1cm} (\text{eq. 11})$$

The switching frequency at nominal load is expressed as:

$$\text{FSW}(\text{load}) = \frac{2 \times I_{\text{OUT}}(V_{\text{OUT}} + V_D - \eta \times V_{\text{IN}})}{I_{\text{PK}}^2 \times L} \hspace{1cm} (\text{eq. 12})$$

Then the maximum output current under the current limit control will be achieved at the limits of critical conduction mode and can be calculated by the equation below:

$$I_{\text{OUT MAX}} = \frac{V_{\text{IN}} \times I_{\text{PK}}}{2 \times (V_{\text{OUT}} + V_D) \times \eta} \hspace{1cm} (\text{eq. 13})$$

This method can achieve larger maximum output current in DCM mode. Since the current limit is reached in each switching cycle, the inductor current ripple is larger resulting in larger output voltage ripple. Two ceramic capacitors in parallel can be used at the output to keep the output ripple small.

The Continuous Conduction Mode

The operation can go beyond the critical conduction mode if the current loading further increases above the maximum output current in DCM mode. However, stable operation in continuous conduction mode is hard to achieve, and double pulsing or group pulsing will occur which will lead to much larger inductor current ripple and result in larger output ripple voltage.

Diode

The diode is the main source of loss in DC–DC converters. The key parameters which affect their efficiency are the forward voltage drop, $V_D$, and the reverse recovery time, $t_{rr}$. The forward voltage drop creates a loss just by having a voltage across the device with a current flowing through it. The reverse recovery time generates a loss when the diode is reverse biased, and the current appears to actually flow backwards through the diode due to the minority carriers being swept from the P–N junction. Care must be taken when choosing a diode. To achieve high efficiency, it is recommended to observe the following rules:

1. Small forward voltage, $V_D < 0.3$ V.
2. Small reverse leakage current.
3. Fast reverse recovery time/switching speed.
4. Rated current larger than peak inductor current, $I_{\text{rated}} > I_{\text{PK}}$.
5. Reverse voltage larger than output voltage, $V_{\text{reverse}} > V_{\text{OUT}}$.

Input Capacitor

The input capacitor stabilizes the input voltage and minimizes peak current ripple from the power source. The capacitor should be connected directly to the inductor pin where the input voltage is applied in order to effectively smooth the input current ripple and voltage due to the inductor current ripple. The input capacitor is also used to decouple the high frequency noise from the $V_{\text{DD}}$ supply to the internal control circuit; therefore, the capacitor should be placed close to the $V_{\text{DD}}$ pin. For some particular applications, separate decoupling capacitors should be provided and connected directly to the $V_{\text{DD}}$ pin for better decoupling effect. A larger input capacitor can better reduce ripple current at the input. By reducing the ripple current at the input, the converter efficiency can be improved. In general, a 4.7 μF to 22 μF ceramic input capacitor is sufficient for most applications. X5R and X7R type ceramic capacitors are recommended due to their good capacitance tolerance and stable temperature behavior.

Output Capacitor

The output capacitor sustains the output voltage by providing the current required by the load and smooths the output ripple voltage. The choice of the output capacitor depends on the application’s requirements for output voltage ripple. Low ESR output capacitors yield better output voltage filtering. Ceramic capacitors are recommended due to their low ESR at high switching frequency and low profile geometry. In general, a 3.3 μF to 22 μF ceramic capacitor should be appropriate for most applications. X5R and X7R type ceramic capacitors are
recommended due to their good capacitance tolerance and
temperature coefficient, while Y5V type ceramic
 capacitors are not recommended since both their
capacitance tolerance and temperature coefficient are too
large. The output voltage ripple at nominal load current can
be calculated by the following equations:

\[ VRIPPLE = I_{PK} \times ESR \]  \hspace{1cm} (eq. 14)

Where \( I_{OUT} \) is the nominal load current, \( C_{OUT} \) is the
selected output capacitance, \( I_{PK} \) is the peak inductor
current, \( L \) is the selected inductance, \( V_{OUT} \) is the output
voltage, \( V_D \) is the Schottky diode forward voltage, \( V_{IN} \)
is the input voltage, and ESR is the ESR of the output
capacitor.

**Feedback Resistors**

To achieve better efficiency at light load, a high
impedance feedback resistor divider should be used.
Choose the lower resistor \( R2 \) value from the range of 10 k\( \Omega \)
to 200 k\( \Omega \). The value of the upper resistor \( R1 \) can then be
calculated from the equation below:

\[ R_1 = R_2 \times \left( \frac{V_{OUT}}{1.19} - 1 \right) \]  \hspace{1cm} (eq. 15)

1%-tolerance resistors should be used for both \( R1 \) and
\( R2 \) for better \( V_{OUT} \) accuracy.

**Feedforward Capacitor**

A feedforward capacitor is required to add across the
upper feedback resistor to avoid double pulsing or group
pulsing at the switching node which will cause larger
inductor ripple current and higher output voltage ripple.
With adequate feedforward capacitance, evenly distributed
single pulses at the switching node can be achieved.
The range of the capacitor value is from 5 pF to 200 pF for most
applications. For NCP1406, the lower the switching
frequency, the larger the feedforward capacitance is
needed. For the initial trial value of the feedforward
capacitor, the following equation can be used; however, the
actual value needs fine tuning:

\[ C_{FF} = \frac{1}{2 \times \pi \times \frac{f_{SW(load)}}{20} \times R_1} \]  \hspace{1cm} (eq. 16)

**PCB Layout Guidelines**

PCB layout is very important for switching converter
performance. All the converter’s external components
should be placed close to the IC. The schematic, PCB
trace layout, and component placement of the step-up
DC–DC converter demonstration board are shown in
Figures 32 through 35 for PCB layout design reference.

The following guidelines should be observed:

1. **Grounding**
   Single-point grounding should be used for the output
   power return ground, the input power return ground, and
   the device switch ground to reduce noise. The input ground
   and output ground traces must be thick and short enough for
current to flow through. A ground plane should be used to
   reduce ground bounce.

2. **Power Traces**
   Low resistance conducting paths (short and thick traces)
   should be used for the power carrying traces to reduce
   power loss so as to improve efficiency (short and thick
   traces for connecting the inductor \( L \) can also reduce stray
   inductance). The path between \( C1, L1, D1, \) and \( C2 \) should
   be kept short. The trace from \( L \) to \( LX \) pin of the IC should
   also be kept short.

3. **External Feedback Components**
   Feedback resistors \( R1 \) and \( R2 \), and feedforward capacitor
   \( C3 \) should be located as close to the FB pin as possible to
   minimize noise picked up by the FB pin. The ground
   connection of the feedback resistor divider should be
   connected directly to the GND pin.

4. **Input Capacitor**
   The input capacitor should be located close to both the
   input to the inductor and the VDD pin of the IC.

5. **Output Capacitor**
   The output capacitor should be placed close to the output
terminals to obtain better smoothing effect on output ripple
voltage.

![Figure 32. Step-Up Converter Demonstration Board Schematic](http://onsemi.com)
Figure 33. Step-Up Converter Demonstration Board
Top Layer Component Silkscreen

Figure 34. Step-Up Converter Demonstration Board
Top Layer Copper

Figure 35. Step-Up Converter Demonstration Board
Bottom Layer Copper
## Components and Suppliers

<table>
<thead>
<tr>
<th>Output Voltage</th>
<th>Parts</th>
<th>Supplier</th>
<th>Part Number</th>
<th>Description</th>
<th>Website</th>
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<td>Panasonic</td>
<td>ECJ2FB0J106M</td>
<td>Ceramic Capacitor 0805, 10 μF/6.3 V</td>
<td><a href="http://www.panasonic.com">www.panasonic.com</a></td>
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<td>TDK</td>
<td>C1608X5R0J475MT</td>
<td>Ceramic Capacitor 0603, 10 μF/6.3 V</td>
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<td>C2</td>
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<td>Ceramic Capacitor 1206, 4.7 μF/25 V</td>
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<td>Schottky Power Rectifier 20 V/500 mA</td>
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<td>CMD4D11−100MC</td>
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<td>25 V Step–up DC–DC Converter</td>
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NCP1406, NCV1406

OTHER APPLICATION CIRCUITS

Figure 36. Positive–to–Negative Output Converter for Negative LCD Bias

Figure 37. +15 V, −15 V Outputs Converter for LCD Bias Supply
Figure 38. +15 V, −7.5 V Outputs Converter for CCD Supply Circuit

Figure 39. White LEDs Driver Circuit
PACKAGE DIMENSIONS

TSOP−5
SN SUFFIX
CASE 483−02
ISSUE H

NOTES:
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
5. OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

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SEATING PLANE

SOLDERING FOOTPRINT*

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.